



| | | | | | | | |
|--|--|---------------------------------|-----------------------------------|----------------------------------|----------|----------------|----|
| INFORMATION DISCLOSURE CITATION PTO-1449 | | Customer Number 26615 | ATTORNEY'S DKT NO. H1492 | APPLICATION No. 10/653,105 | | | |
| | | | APPLICANT(S) Bin Yu et al. | | | | |
| | | | FILING DATE September 3, 2003 | GROUP 2829 2811 | | | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAMINER'S INITIALS | PATENT NO. | DATE | NAME | CLASS | SUBCLASS | FILING DATE | |
| <u>Nu</u> | US 2002/0125536 A1 | 09-12-02 | Iwasa et al. | 257 | 368 | 07-18-01 | |
| <u>Vu</u> | US 2002/0153587 A1 | 10-24-02 | Adkisson et al. | 257 | 510 | 07-02-02 | |
| <u>Vu</u> | US 2002/0177263 A1 | 11-28-02 | Hanafi et al. | 438 | 183 | 05-24-01 | |
| <u>Vu</u> | 6,359,311 B1 | 03-19-02 | Colinge et al. | 257 | 347 | 01-17-01 | |
| FOREIGN PATENT DOCUMENTS | | | | | | | |
| EXAMINER'S INITIALS | PATENT NO. | DATE | COUNTRY | CLASS | SUBCLASS | Translation | |
| | | | | | | Yes | No |
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | |
| <u>Nu</u> | Jong-Tae Park et al.: "Multiple-Gate SOI MOSFETs: Device Design Guidelines," <i>IEEE Transactions on Electron Devices</i> , Vol. 49, No. 12, December 2002, pp. 2222-2229. | | | | | | |
| | Fu-Liang Yang et al.: "25 nm CMOS Omega FETs," International Electron Devices Meeting 2002, IEDM, Technical Digest, December 8-11, 2002 in New York, NY, pp. 255-258. | | | | | | |
| | Toshikazu Mukaiyama et al.: "Fabrication of Gate-All-Around MOSFET By Silicon Anisotropic Etching Technique," <i>Solid State Electronics</i> , Elsevier Science Publishers, Vol. 42, No. 7-8, July 8, 1998, pp. 1623-1626. | | | | | | |
| | Yang-Kyu Choi et al.: "Spacer FinFET: nanoscale double-gate CMOS technology for the terabit era," <i>Solid State Electronics</i> , Elsevier Science Publishers, Vol. 46, No. 10, October 2002, pp. 1595-1601. | | | | | | |
| | Effendi Leobandung et al.: "Wire-channel and wrap-around-gate metal-oxide-semiconductor field-effect transistors with a significant reduction of short channel effects," 41 st International Conference on Electron, Ion, and Photon Beams Technology and Nanofabrication in Dana Point, CA, May 27-30, 1997, Vol. 15, No. 6, <i>Journal of Vacuum Science & Technology B</i> (Microelectronics and Nanometer Structures), November-December 1997, AIP for American Vacuum Soc., pp. 2791-2794. | | | | | | |
| <u>Vu</u> | PCT International Search Report mailed July 13, 2004, 5 pages. | | | | | | |
| EXAMINER HUNG VU | | | DATE CONSIDERED 8/02/04 | | | | |

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).